



Air Force Invention No. AFB00670

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On 16 November 2004
(DATE OF DEPOSIT)

WILLIAM G. AUTON 31,320
NAME OF APPLICANT, ASSIGNEE, OR REG. REP.


16 November 2004
SIGNATURE DATE

In re application of
Richard A. Soref
Application Serial No. 10/722,611
Filed: 28 November 2003

Examiner: Allan Wilson
Art Unit: 2815

For: **STRAIN-ENGINEERED DIRECT-GAP $\text{Ge/Sn}_x\text{Ge}_{1-x}$ HETERODIODE AND
MULTI-QUANTUM-WELL PHOTODETECTORS, LASERS, EMITTERS AND
MODULATORS GROWN ON $\text{Sn}_y\text{Si}_z\text{Ge}_{1-y-z}$ -BUFFERED SILICON**

Honorable Commissioner of Patents
Alexandria, VA. 22313-1450

AMENDMENT

In response to the Office Action of 12 October 2004, please consider the following amendment.